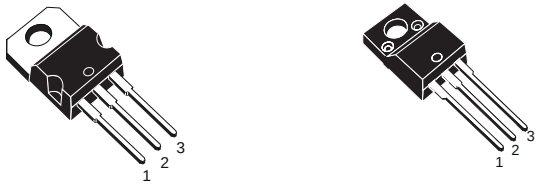
STP11NM60 - STP11NM60FP
STB11NM60 - STB11NM60-1

N-CHANNEL 600V - 0.4Ω-11A TO-220/TO-220FP/D²PAK/I²PAK
MDmesh™ Power MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STP11NM60	600 V	< 0.45 Ω	11 A
STP11NM60FP	600 V	< 0.45 Ω	11 A
STB11NM60	600 V	< 0.45 Ω	11 A
STB11NM60-1	600 V	< 0.45 Ω	11 A

- TYPICAL $R_{DS}(on)$ = 0.4Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- 100% AVALANCHE TESTED
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE



TO-220 TO-220FP



D²PAK I²PAK

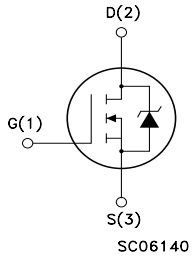
DESCRIPTION

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

APPLICATIONS

The MDmesh™ family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP(B)11NM60(-1)	STP11NM60FP	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	600		V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	600		V
V_{GS}	Gate- source Voltage	±30		V
I_D	Drain Current (continuous) at T_C = 25°C	11	11 (*)	A
I_D	Drain Current (continuous) at T_C = 100°C	7	7 (*)	A
I_{DM} (•)	Drain Current (pulsed)	44	44 (*)	A
P_{TOT}	Total Dissipation at T_C = 25°C	160	35	W
	Derating Factor	1.28	0.28	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	15		V/ns
V_{ISO}	Insulation Winthstand Voltage (DC)	--	2500	V
T_{stg}	Storage Temperature	–65 to 150		°C
T_j	Max. Operating Junction Temperature	150		°C

(•)Pulse width limited by safe operating area

(*)Limited only by maximum temperature allowed

(1)I_{SD}<11A, di/dt<400A/µs, V_{DD}<$V_{(BR)DSS}$, T_J<T_{JMAX}

THERMAL DATA

			TO-220/D²PAK/I²PAK	TO-220FP	
Rthj-case	Thermal Resistance Junction-case	Max	0.78	3.57	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5		°C/W
T_l	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	5.5	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	350	mJ

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	600			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating			1	µA
		V_{DS} = Max Rating, T_C = 125 °C			10	µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ±30V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 5.5A		0.4	0.45	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max}$, I_D = 5.5A		5.2		S
C_{iss}	Input Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		1000		pF
C_{oss}	Output Capacitance			230		pF
C_{rss}	Reverse Transfer Capacitance			25		pF
$C_{oss\ eq.}$ (2)	Equivalent Output Capacitance	V_{GS} = 0V, V_{DS} = 0V to 480V		100		pF
R_G	Gate Input Resistance	f=1 MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.6		Ω

1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 300V, I_D = 5.5A R_G = 4.7Ω V_{GS} = 10V (see test circuit, Figure 3)		20		ns
t_r	Rise Time			20		ns
Q_g	Total Gate Charge	V_{DD} = 400V, I_D = 11A, V_{GS} = 10V		30		nC
Q_{gs}	Gate-Source Charge			10		nC
Q_{gd}	Gate-Drain Charge			15		nC

SWITCHING OFF

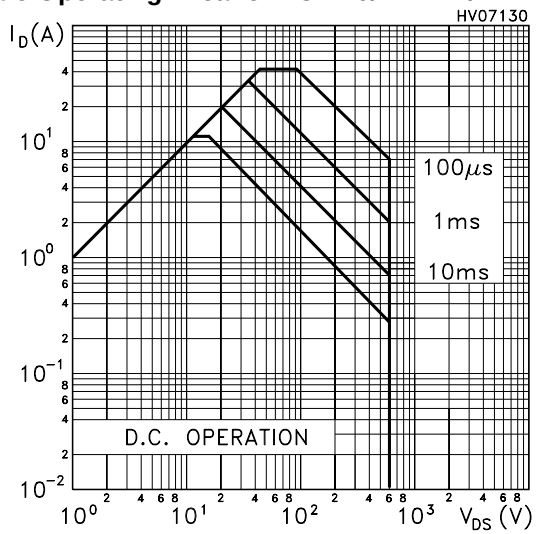
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	V_{DD} = 400V, I_D = 11A, R_G = 4.7Ω, V_{GS} = 10V (see test circuit, Figure 5)		6		ns
t_f	Fall Time			11		ns
t_c	Cross-over Time			19		ns

SOURCE DRAIN DIODE

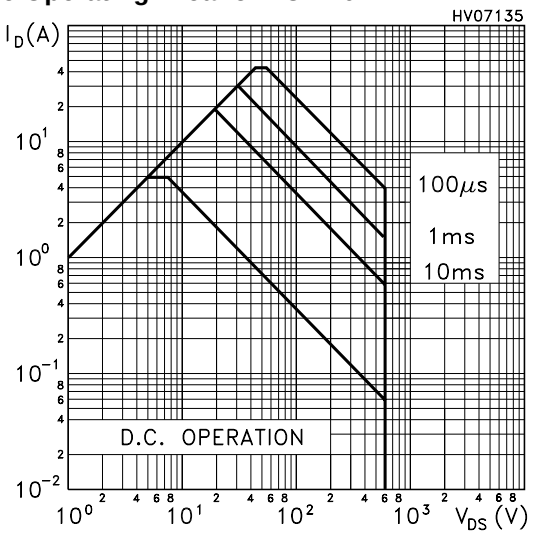
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				11	A
I_{SDM} (2)	Source-drain Current (pulsed)				44	A
V_{SD} (1)	Forward On Voltage	I_{SD} = 11A, V_{GS} = 0			1.5	V
t_{rr} Q_{rr} I_{rrm}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 11A, di/dt = 100A/µs, V_{DD} = 100 V, T_j = 25°C (see test circuit, Figure 5)		390 3.8 19.5		ns µC A
t_{rr} Q_{rr} I_{rrm}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 11A, di/dt = 100A/µs, V_{DD} = 100 V, T_j = 150°C (see test circuit, Figure 5)		570 5.7 20		ns µC A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

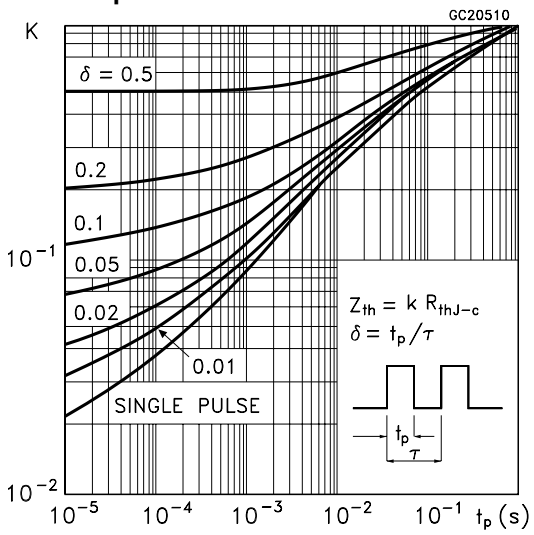
Safe Operating Area for TO-220/D2PAK/I2PAK



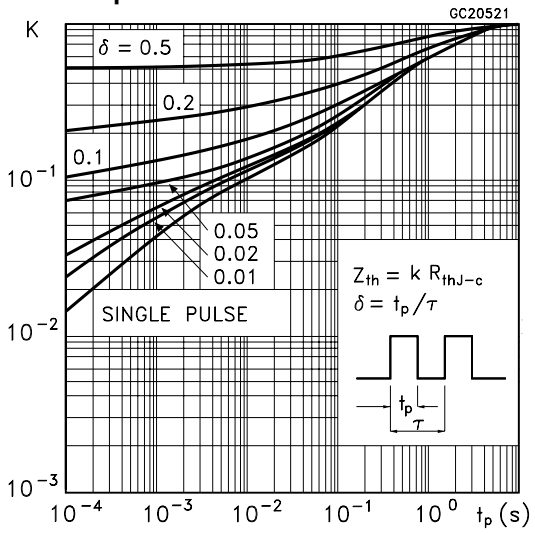
Safe Operating Area for TO-220FP



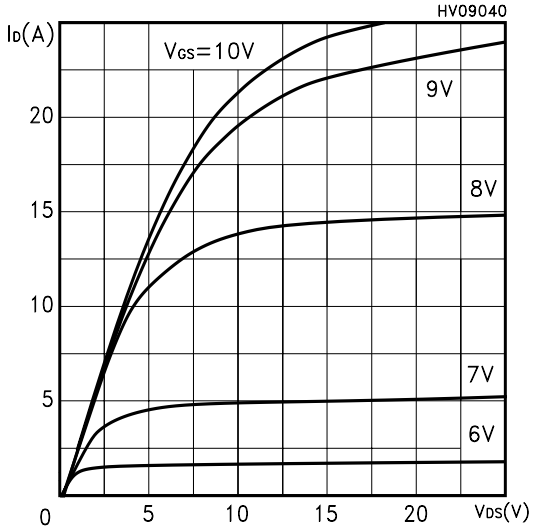
Thermal Impedance for TO-220/D2PAK/I2PAK



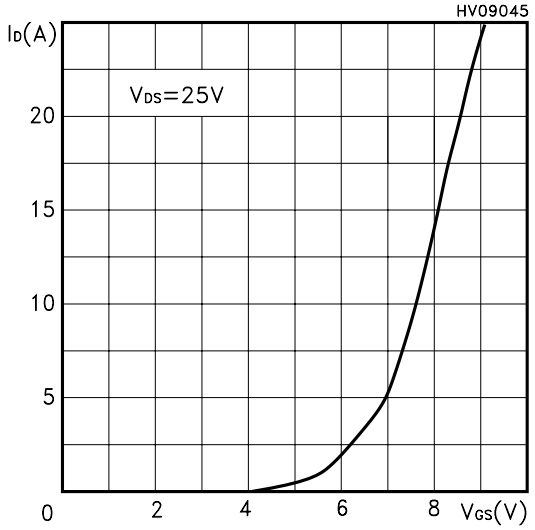
Thermal Impedance for TO-220FP



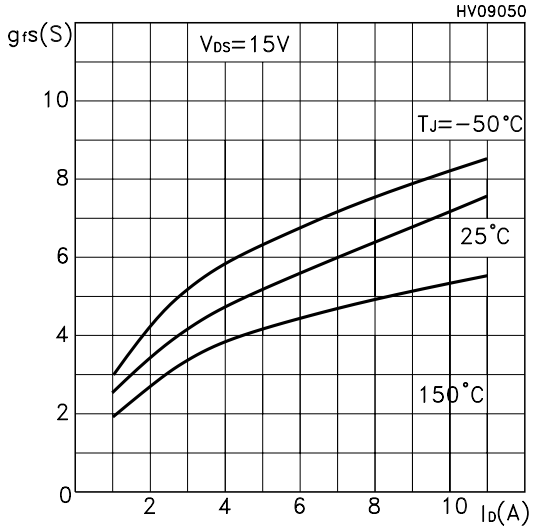
Output Characteristics



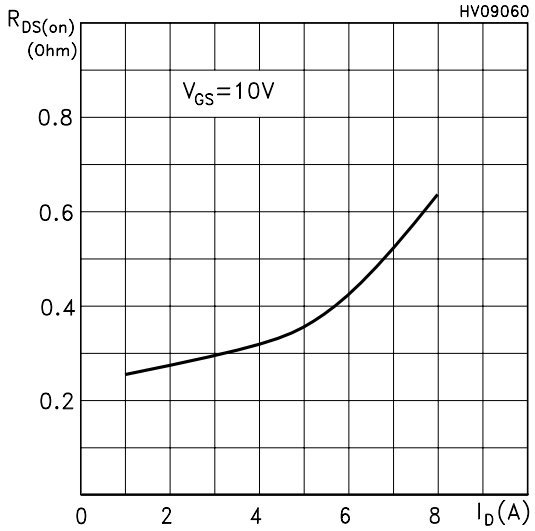
Transfer Characteristics



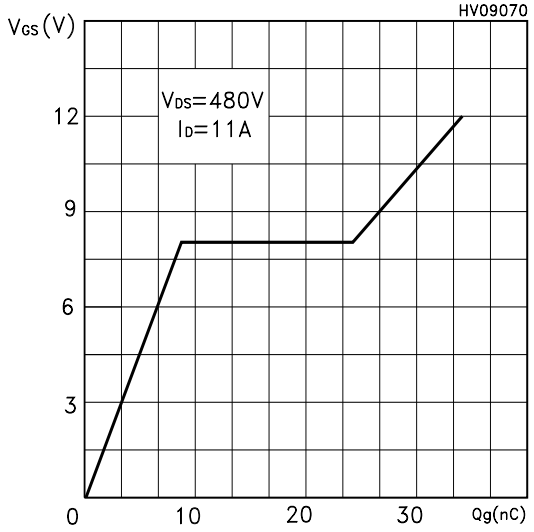
Transconductance



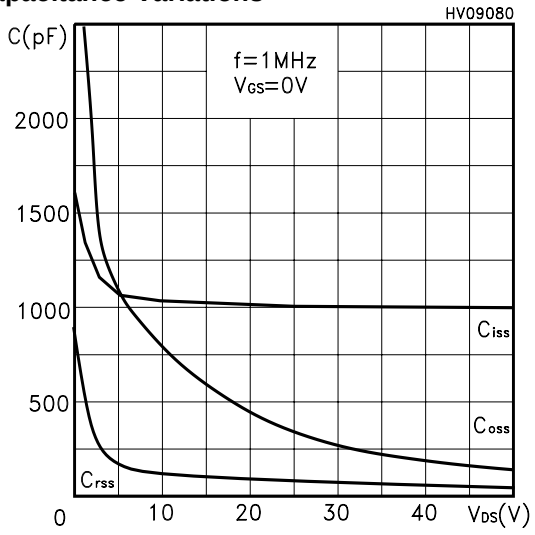
Static Drain-source On Resistance



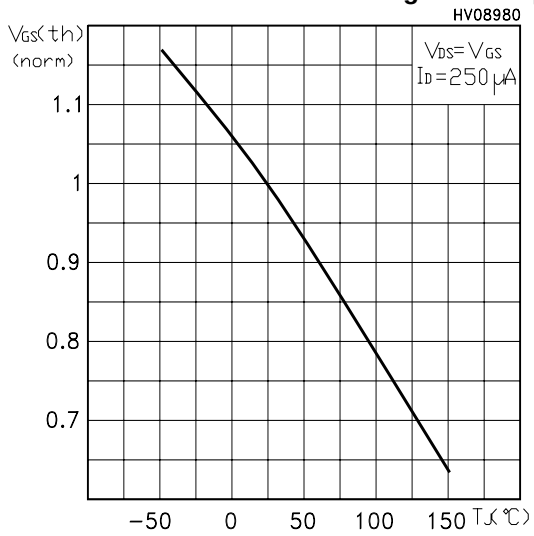
Gate Charge vs Gate-source Voltage



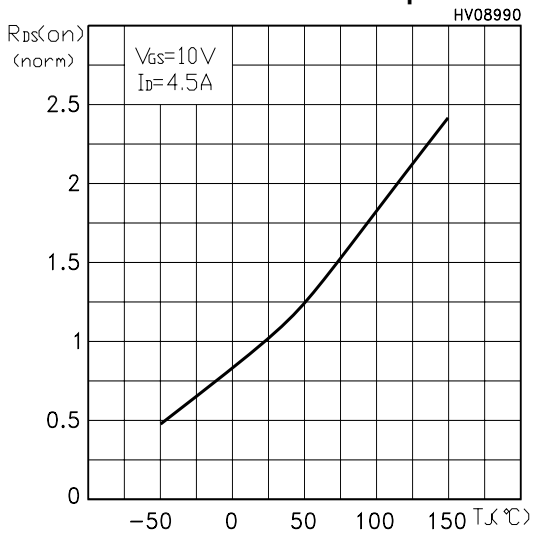
Capacitance Variations



Normalized Gate Thereshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

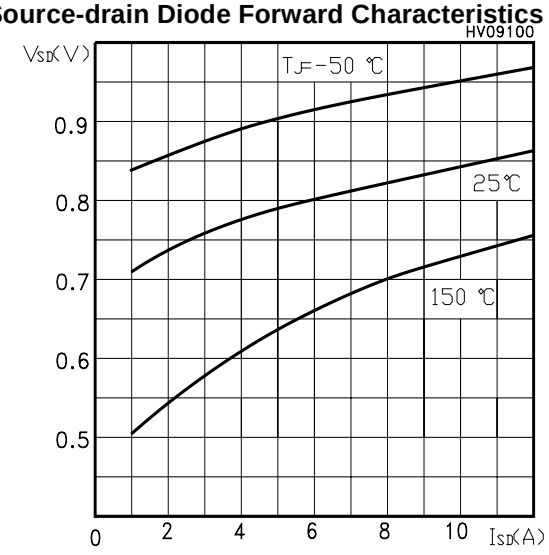


Fig. 1: Unclamped Inductive Load Test Circuit

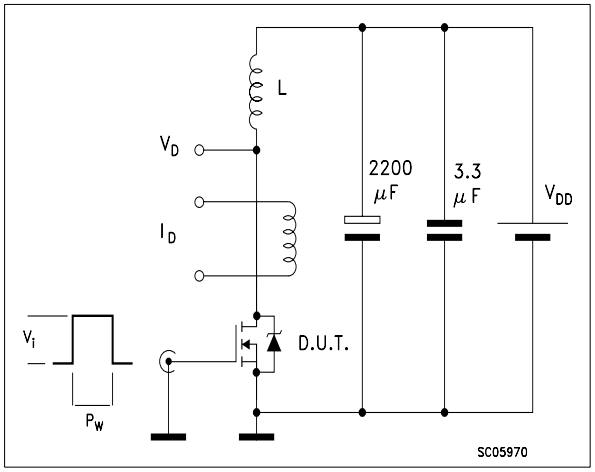


Fig. 2: Unclamped Inductive Waveform

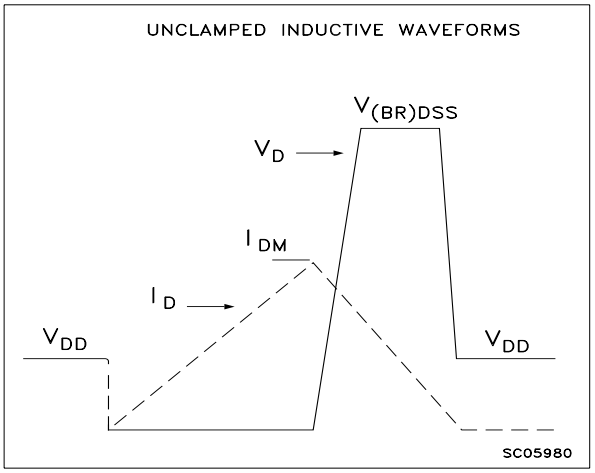


Fig. 3: Switching Times Test Circuit For Resistive Load

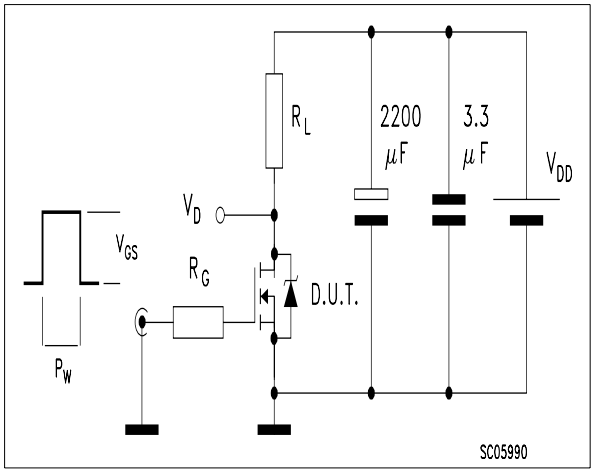


Fig. 4: Gate Charge test Circuit

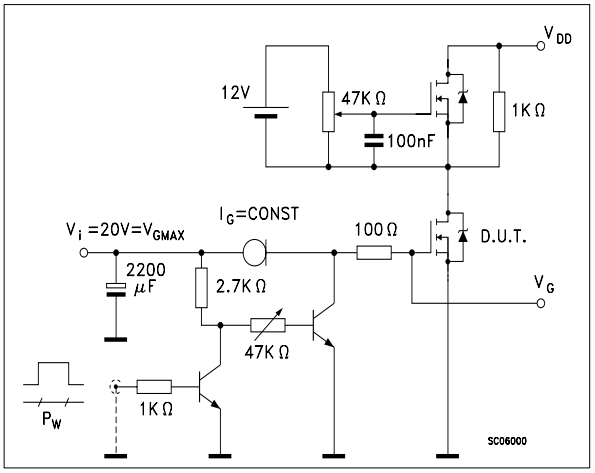
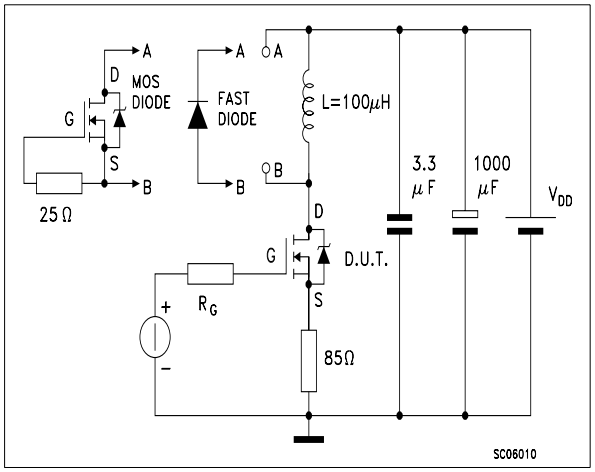
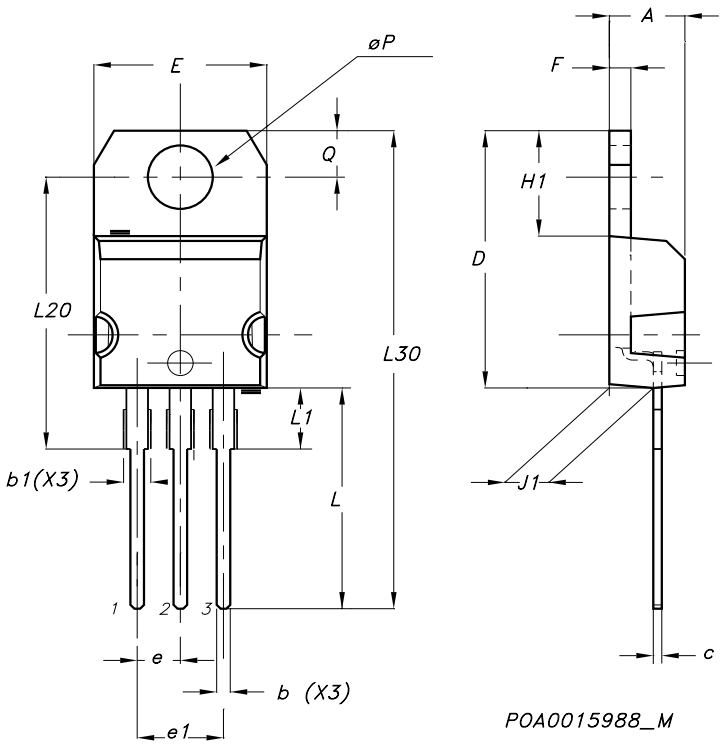


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



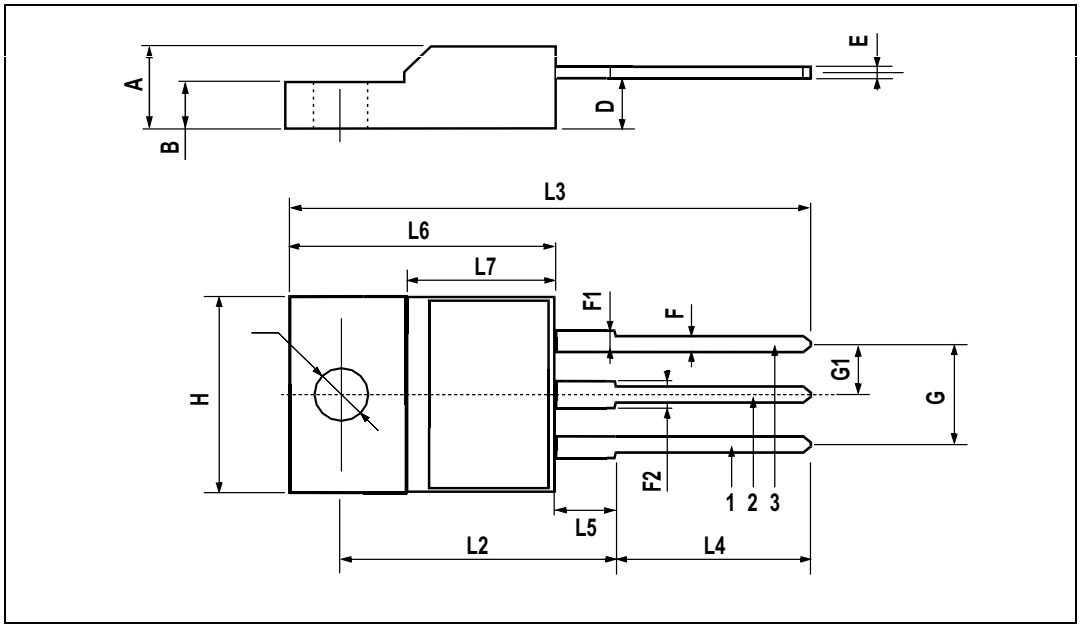
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



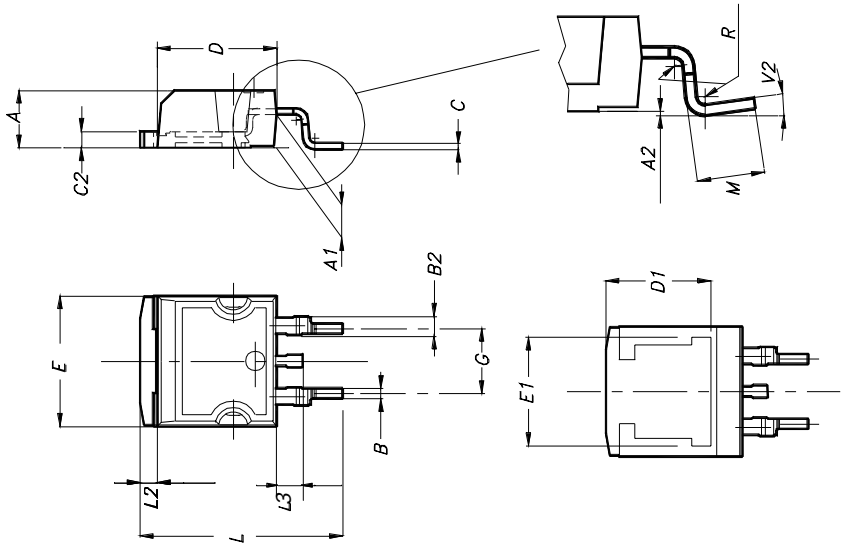
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



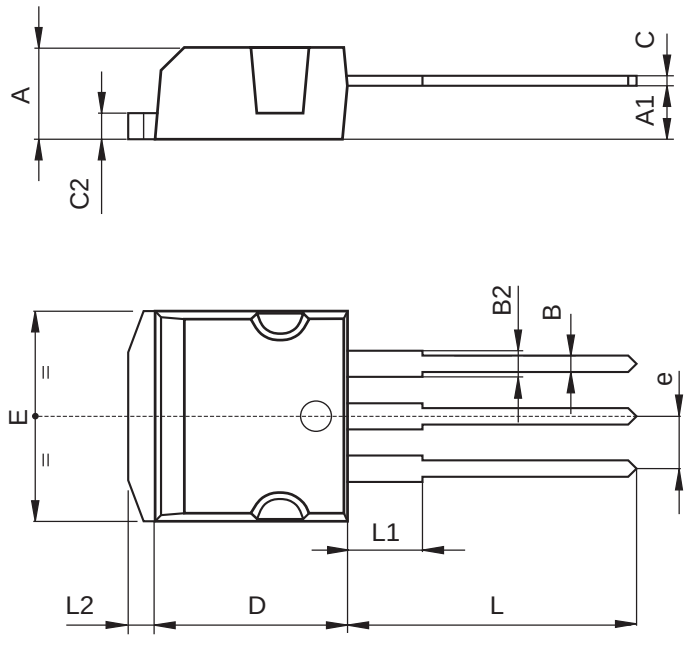
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		8º			



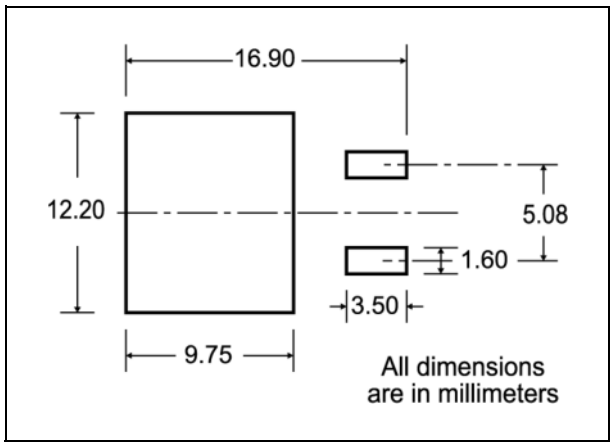
TO-262 (I^2PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
e	2.4		2.7	0.094		0.106
E	10		10.4	0.393		0.409
L	13.1		13.6	0.515		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.4	0.050		0.055

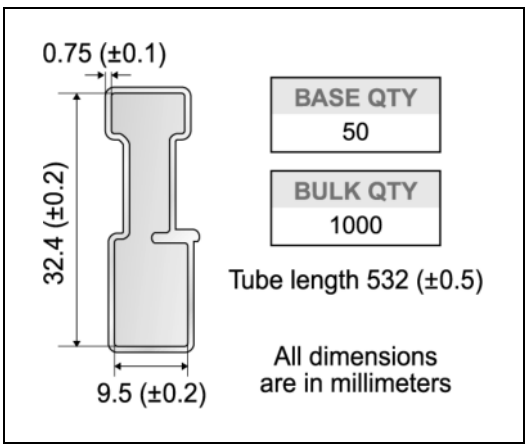


P011P5/E

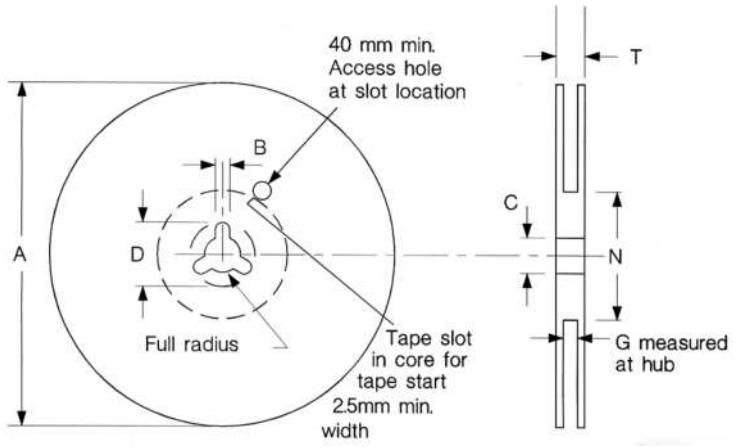
D^2PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



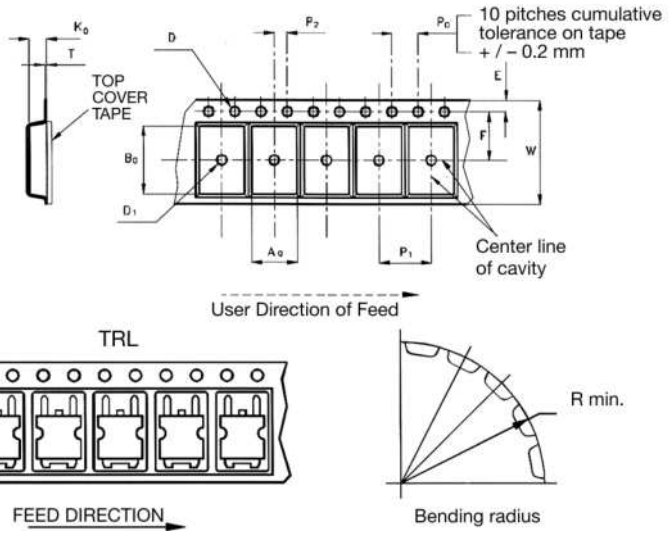
REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956



* on sales type

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